



GMA01, 01U

Epitaxial Planar Silicon Diode
**Very High-Speed Switching,
 Bias Stabilizing Applications**

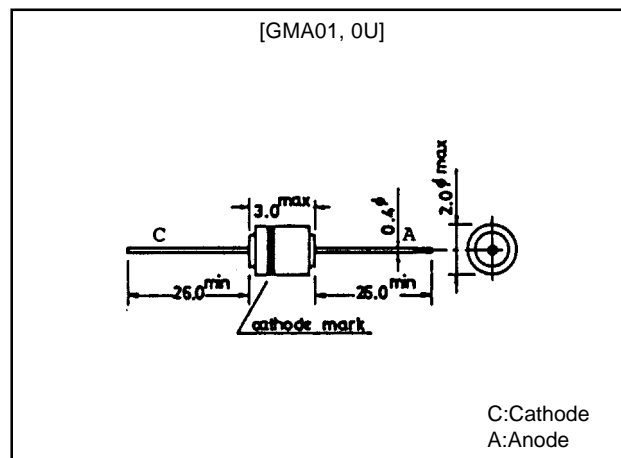
Features

- Glass sleeve structure.
- Allowable power dissipation : $P=300\text{mW}$ max.
- Interterminal capacitance : $c=3.0\text{pF}$ max.
- Reverse recovery time : $t_{rr}=4.0\text{ns}$ max.
- Small size, being about half of DO-35 package heretofore in use.

Package Dimensions

unit:mm

1114



Specifications

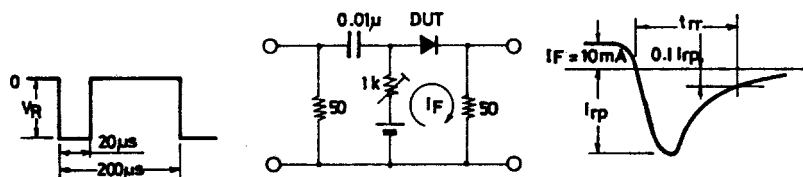
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	GMA01	GMA01U	Unit
Peak Reverse Voltage	V_{RM}		60	105	V
Reverse Voltage	V_R		55	100	V
Peak Forward Current	I_{FM}		→	360	mA
Average Rectified Current	I_O		→	120	mA
Surge Forward Current	I_{FSM}	1 s pulse	→	500	mA
Allowable Power Dissipation	P		→	300	mW
Junction Temperature	T_j		→	175	$^\circ\text{C}$
Storage Temperature	T_{stg}		→	-65 to +175	$^\circ\text{C}$

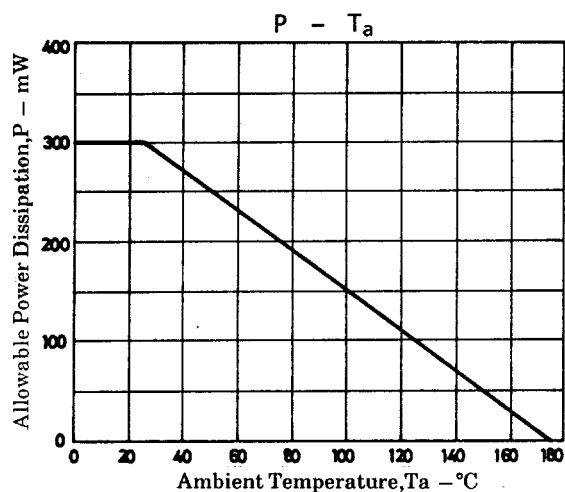
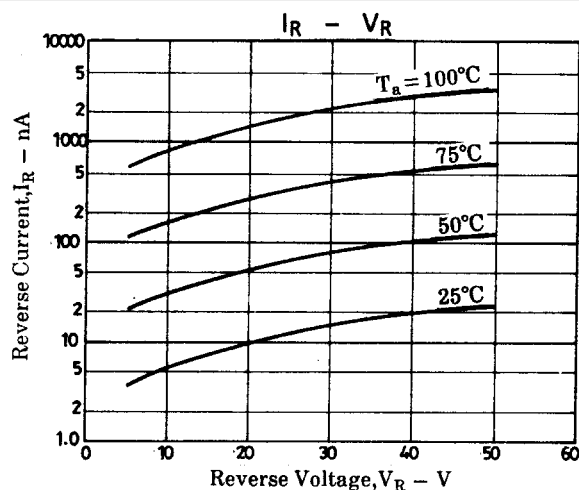
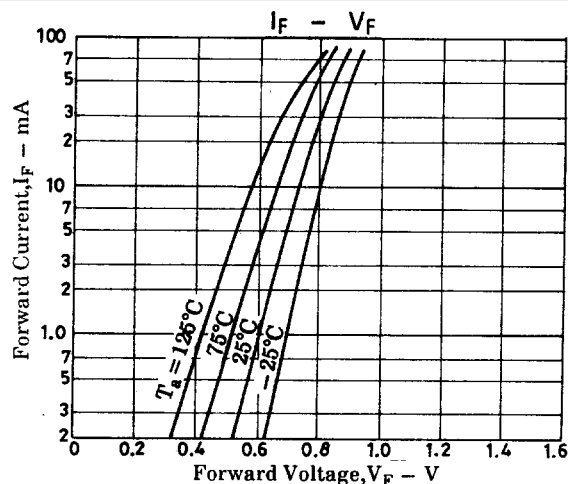
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	$I_F=1.5\text{mA}$	0.55		0.68	V
Reverse Current	I_R	$V_R=55$ (GMA01)			0.5	μA
		$V_R=75$ (GMA01U)			0.5	μA
		$V_R=100\text{V}$ (GMA01U)			5	μA
Interterminal Capacitance	C	$V_R=0$, $f=1\text{MHz}$			3.0	pF
Reverse Recovery Time	t_{rr}	$V_R=6\text{V}$, $I_F=10\text{mA}$, $R_L=50\Omega$			4.0	ns

Reverse Recovery Time Test Circuit

Unit (resistance : Ω , capacitance : F)

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